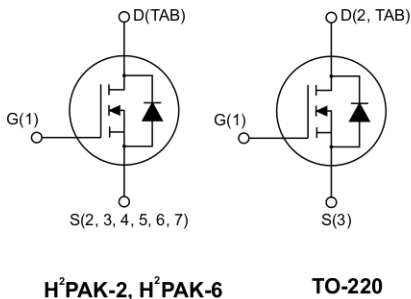
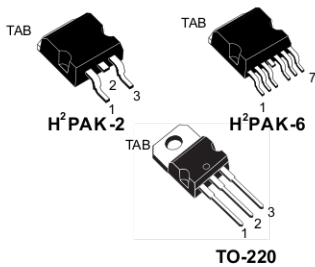


N-channel 80 V, 0.0017 Ω typ., 180 A STripFET F7 Power MOSFETs in an H²PAK-2, H²PAK-6 and TO-220 packages



H2PAK_2_6_N-CHG1DTABS234567_TO-220_N-CHG1D2TABS3



Features

Order codes	V_{DS}	$R_{DS(on)}$ max.	I_D
STH270N8F7-2	80 V	0.0021 Ω	180 A
STH270N8F7-6			
STP270N8F7		0.0025 Ω	

- Among the lowest $R_{DS(on)}$ on the market
- Excellent FoM (figure of merit)
- Low C_{rSS}/C_{iSS} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

These N-channel Power MOSFETs utilize STripFET F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Product status links

[STH270N8F7-2](#)

[STH270N8F7-6](#)

[STP270N8F7](#)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	80	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	180	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	180	A
$I_{DM}^{(2)}$	Drain current (pulsed)	720	A
$P_{TOT}^{(3)}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	315	W
$E_{AS}^{(4)}$	Single pulse avalanche energy	1.16	J
T_j	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature range		

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. This value is rated according to R_{thJC}
4. Starting $T_j=25\text{ }^\circ\text{C}$, $I_D=65\text{ A}$, $V_{DD}=50\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		H ² PAK-2, H ² PAK-6	TO-220	
R_{thJC}	Thermal resistance, junction-to-case	0.48		$^\circ\text{C}/\text{W}$
$R_{thJB}^{(1)}$	Thermal resistance, junction-to-board	35		$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance, junction-to-ambient		62.5	$^\circ\text{C}/\text{W}$

1. When mounted on an 1 inch² FR-4, 2 Oz copper board.

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	80			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 80\text{ V}$			10	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 80\text{ V}$, $T_C = 125\text{ °C}$ ⁽¹⁾			100	μA
I_{GSS}	Gate-body leakage current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	For H ² PAK-2, H ² PAK-6: $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$		0.0017	0.0021	Ω
		For TO-220: $V_{GS} = 10\text{ V}$, $I_D = 90\text{ A}$		0.0021	0.0025	

1. Defined by design, not subject to production test.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	13600	-	pF
C_{oss}	Output capacitance		-	2050	-	pF
C_{rss}	Reverse transfer capacitance		-	236	-	pF
Q_g	Total gate charge	$V_{DD} = 40\text{ V}$, $I_D = 180\text{ A}$,	-	193	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	96	-	nC
Q_{gd}	Gate-drain charge	(see Figure 20. Test circuit for gate charge behavior)	-	46	-	nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 40\text{ V}$, $I_D = 90\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 19. Test circuit for resistive load switching times and Figure 24. Switching time waveform)	-	56	-	ns
t_r	Rise time		-	180	-	ns
$t_{d(off)}$	Turn-off delay time		-	98	-	ns
t_f	Fall time		-	42	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		180	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		720	A
$V_{SD}^{(2)}$	Source-drain current	$I_{SD} = 90\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 180\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	78		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 64\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 21. Test circuit for inductive load switching and diode recovery times)	-	182		nC
I_{RRM}	Reverse recovery current		-	4.7		A

1. Pulse width limited by safe operating area.

2. Pulsed: pulse duration=300 μs , duty cycle 1.5%.

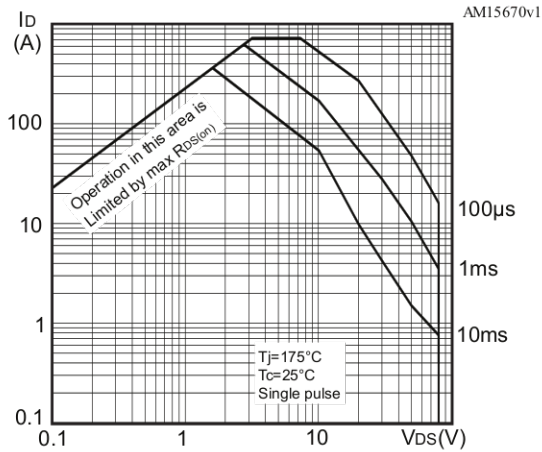
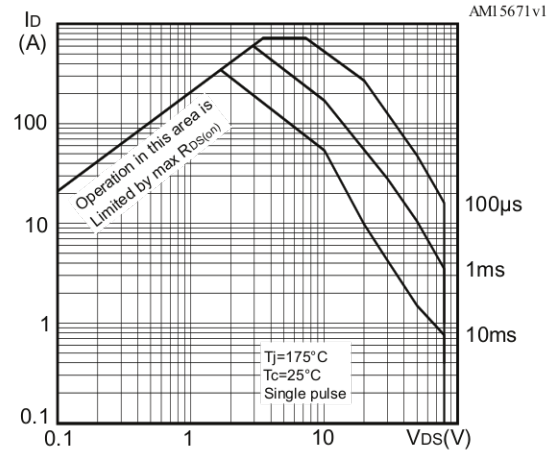
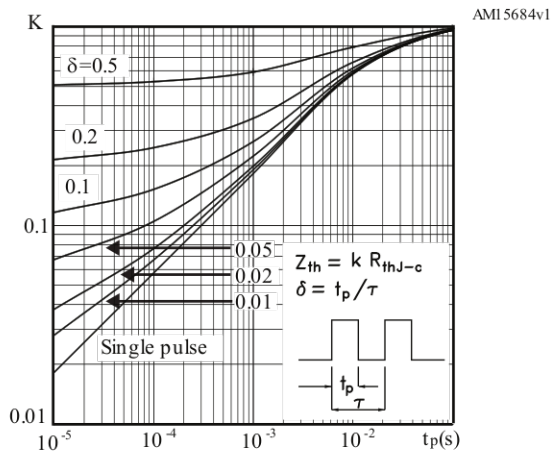
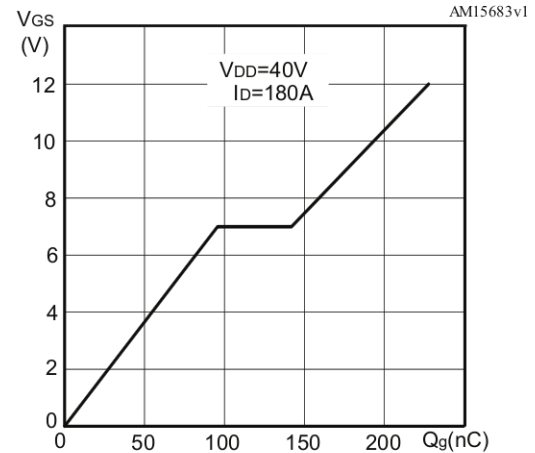
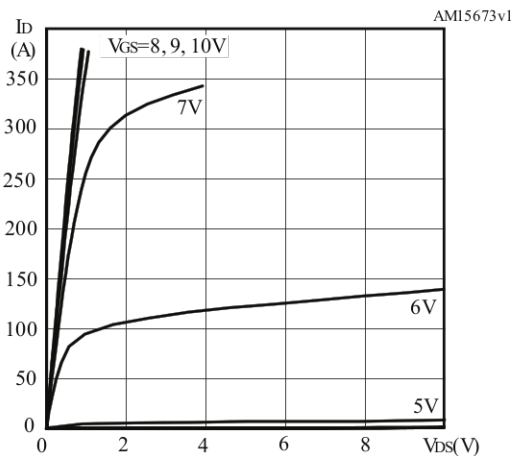
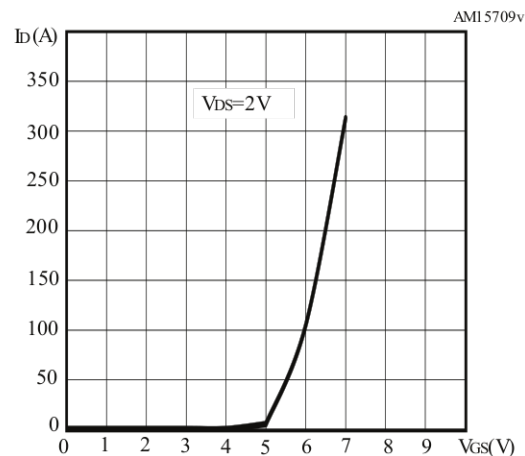
2.1 Electrical characteristics (curves)
Figure 1. Safe operating area for H²PAK-2 and H²PAK-6

Figure 2. Safe operating area for TO-220

Figure 3. Normalized transient thermal impedance

Figure 4. Typical gate charge characteristics

Figure 5. Typical output characteristics for TO-220

Figure 6. Typical transfer characteristics for TO-220


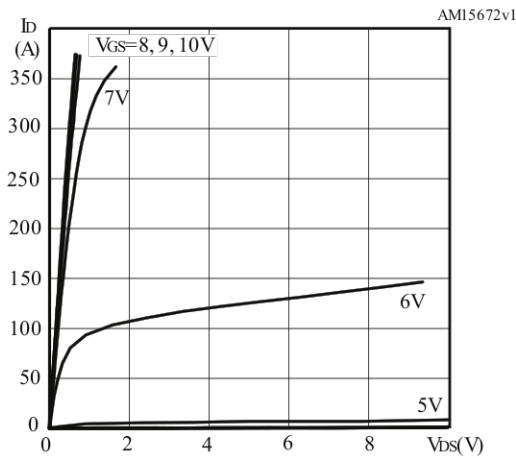
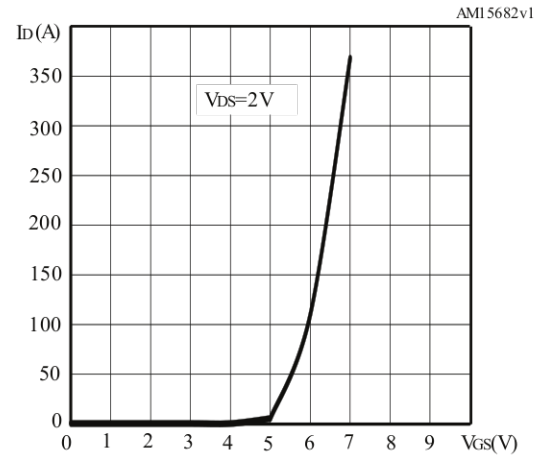
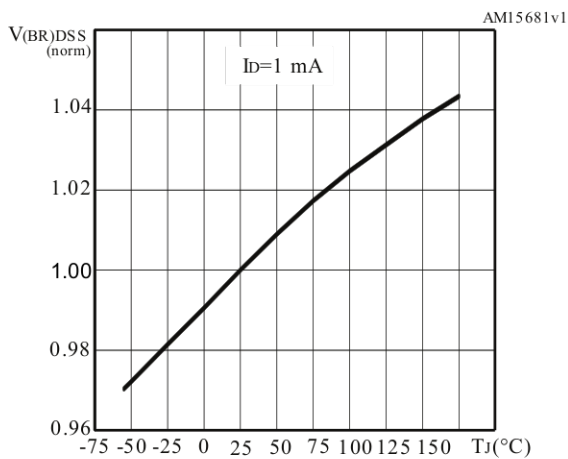
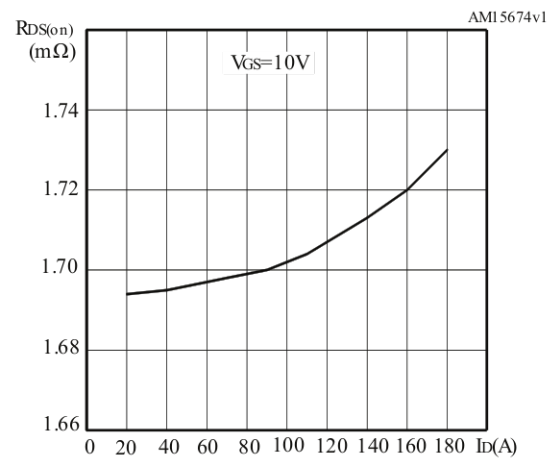
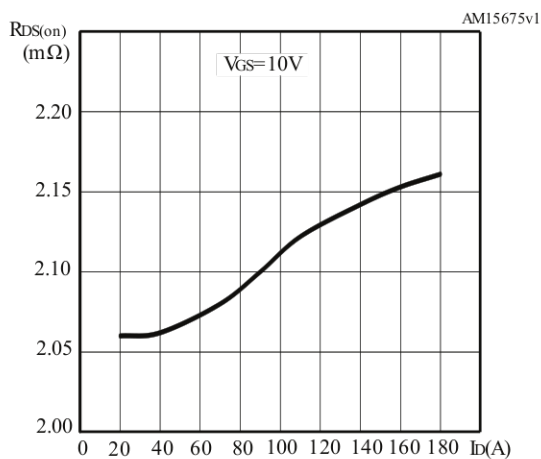
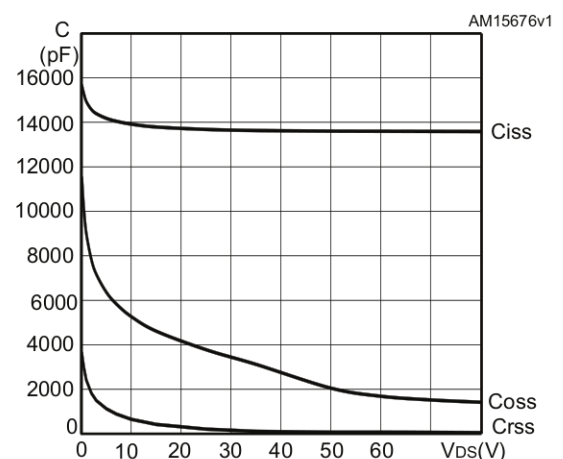
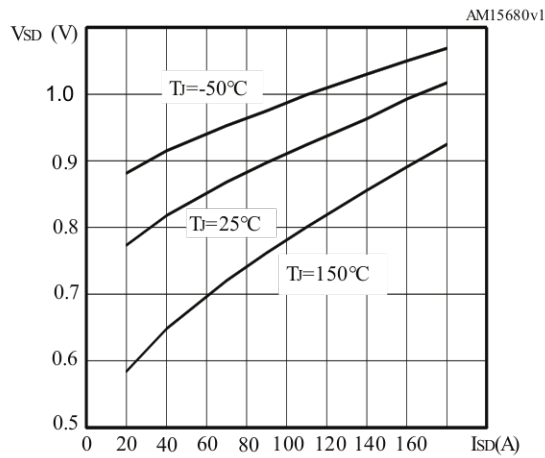
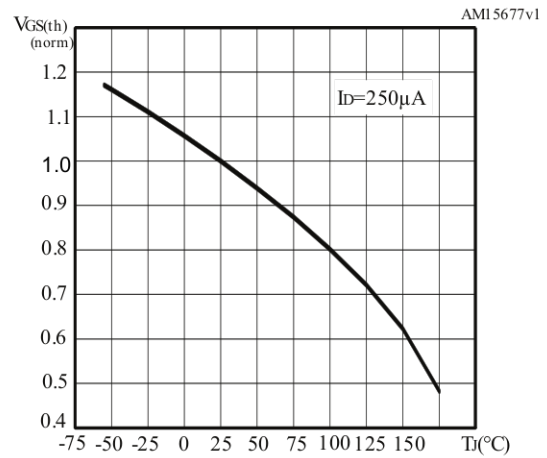
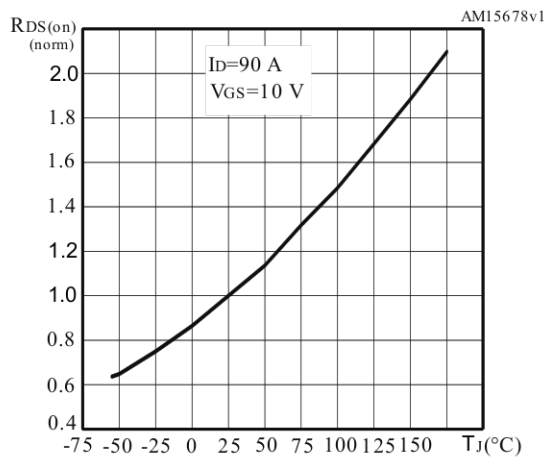
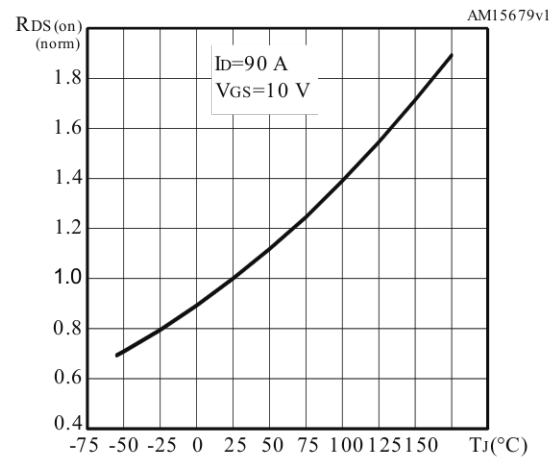
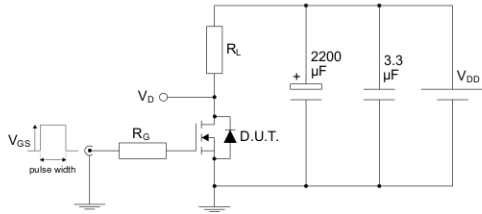
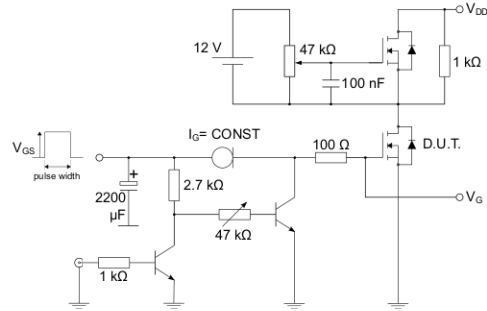
Figure 7. Typical output characteristics for H²PAK-2 and H²PAK-6

Figure 8. Typical transfer characteristics for H²PAK-2 and H²PAK-6

Figure 9. Normalized breakdown voltage vs temperature

Figure 10. Typical drain-source on-resistance for H²PAK-2 and H²PAK-6

Figure 11. Typical drain-source on-resistance for TO-220

Figure 12. Typical capacitance characteristics


Figure 13. Typical reverse diode forward characteristics

Figure 14. Normalized gate threshold vs temperature

Figure 15. Normalized on-resistance vs temperature for H²PAK-2 and H²PAK-6

Figure 16. Normalized on-resistance vs temperature for TO-220


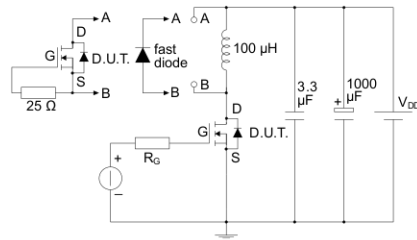
3 Test circuits

Figure 17. Test circuit for resistive load switching times


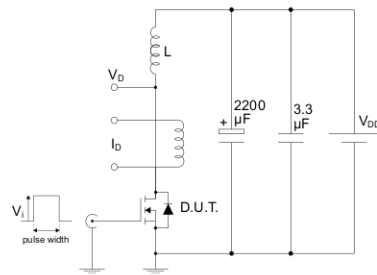
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Figure 18. Test circuit for gate charge behavior


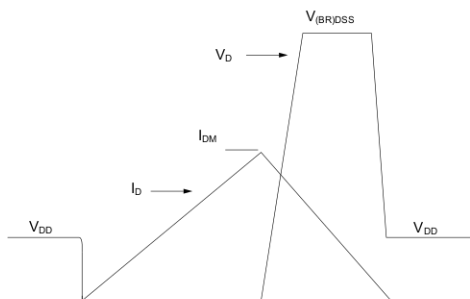
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Figure 19. Test circuit for inductive load switching and diode recovery times


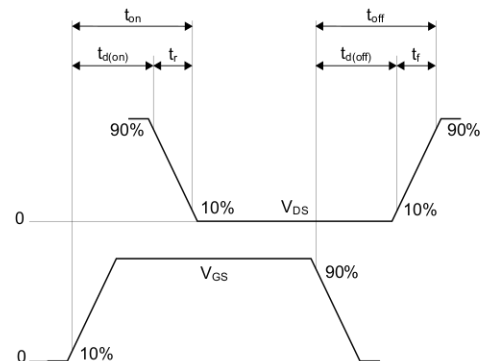
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Figure 20. Unclamped inductive load test circuit


AM01471v1

Figure 21. Unclamped inductive waveform


AM01472v1

Figure 22. Switching time waveform


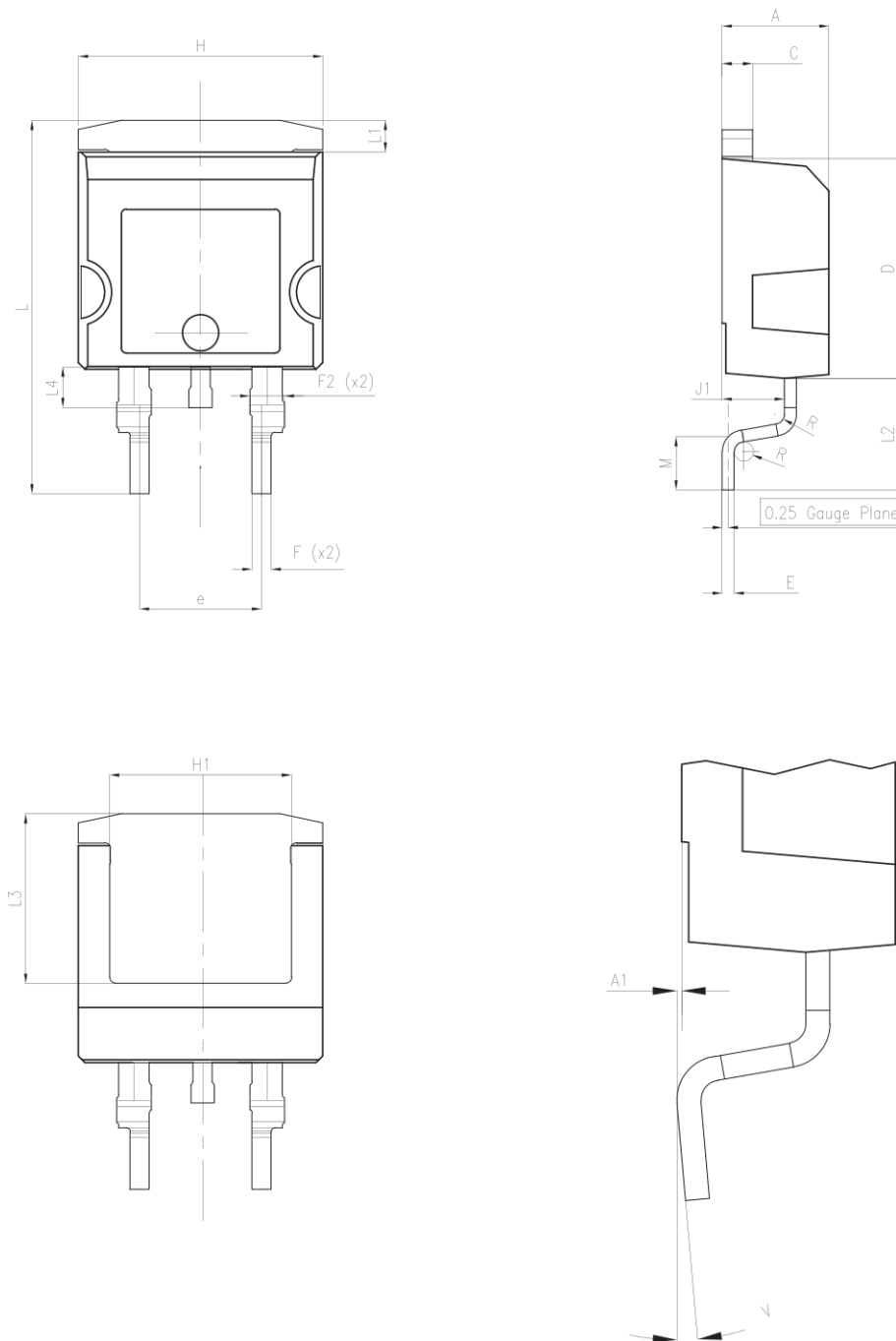
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 H²PAK-2 package information

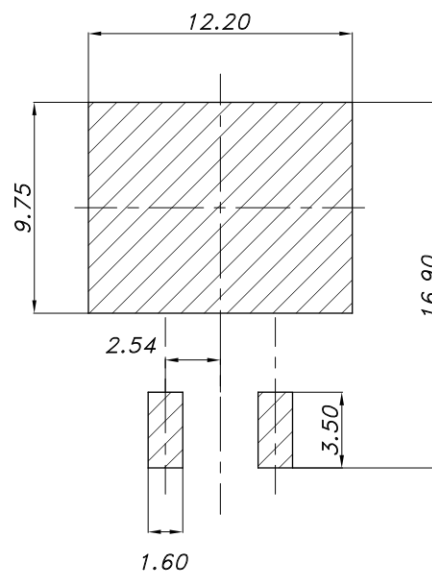
Figure 23. H²PAK-2 package outline



8159712_9

Table 7. H²PAK-2 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.70
A1	0.03		0.20
C	1.17		1.37
D	8.95		9.35
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
F2	1.14		1.70
H	10.00		10.40
H1	7.40	-	7.80
J1	2.49		2.69
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.50		1.70
M	2.60		2.90
R	0.20		0.60
V	0°		8°

Figure 24. H²PAK-2 recommended footprint


8159712_9

Note: Dimensions are in mm.

4.2 H²PAK-6 package information

Figure 25. H²PAK-6 package outline

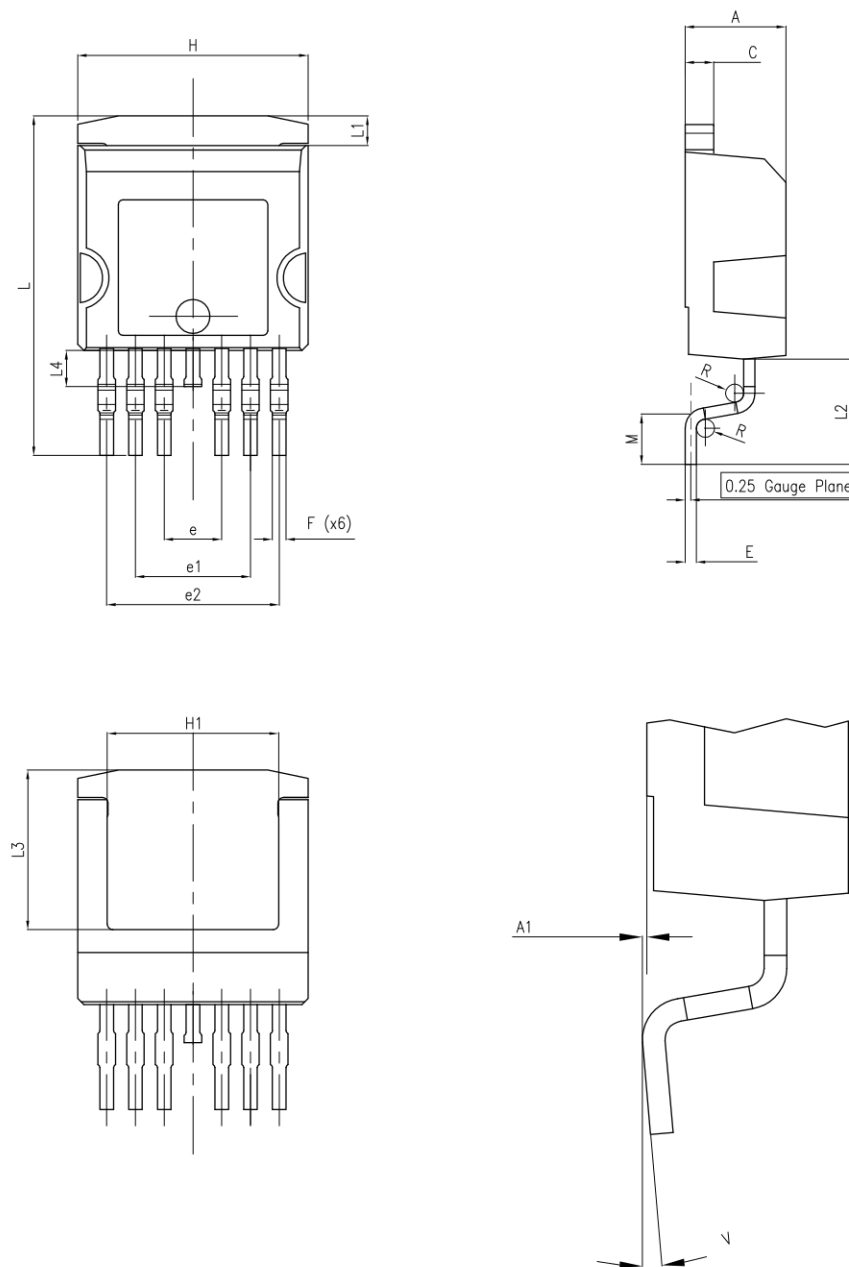
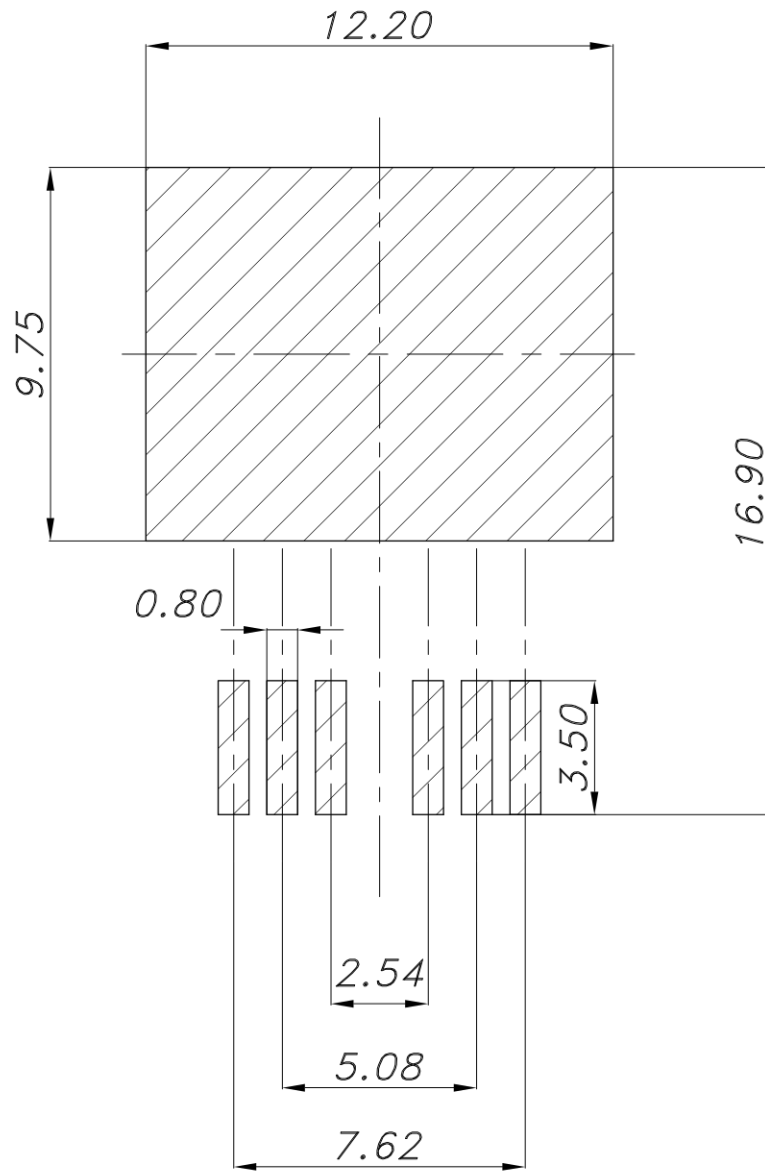


Table 8. H²PAK-6 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.70
A1	0.03		0.20
C	1.17		1.37
e	2.34	2.54	2.74
e1	4.88		5.28
e2	7.42		7.82
E	0.45		0.60
F	0.50		0.70
H	10.00		10.40
H1	7.40		7.80
L	14.75		15.25
L1	1.27		1.40
L2	4.35		4.95
L3	6.85		7.25
L4	1.50		1.75
M	1.90		2.50
R	0.20		0.60
V	0°		8°

Figure 26. H²PAK-6 recommended footprint

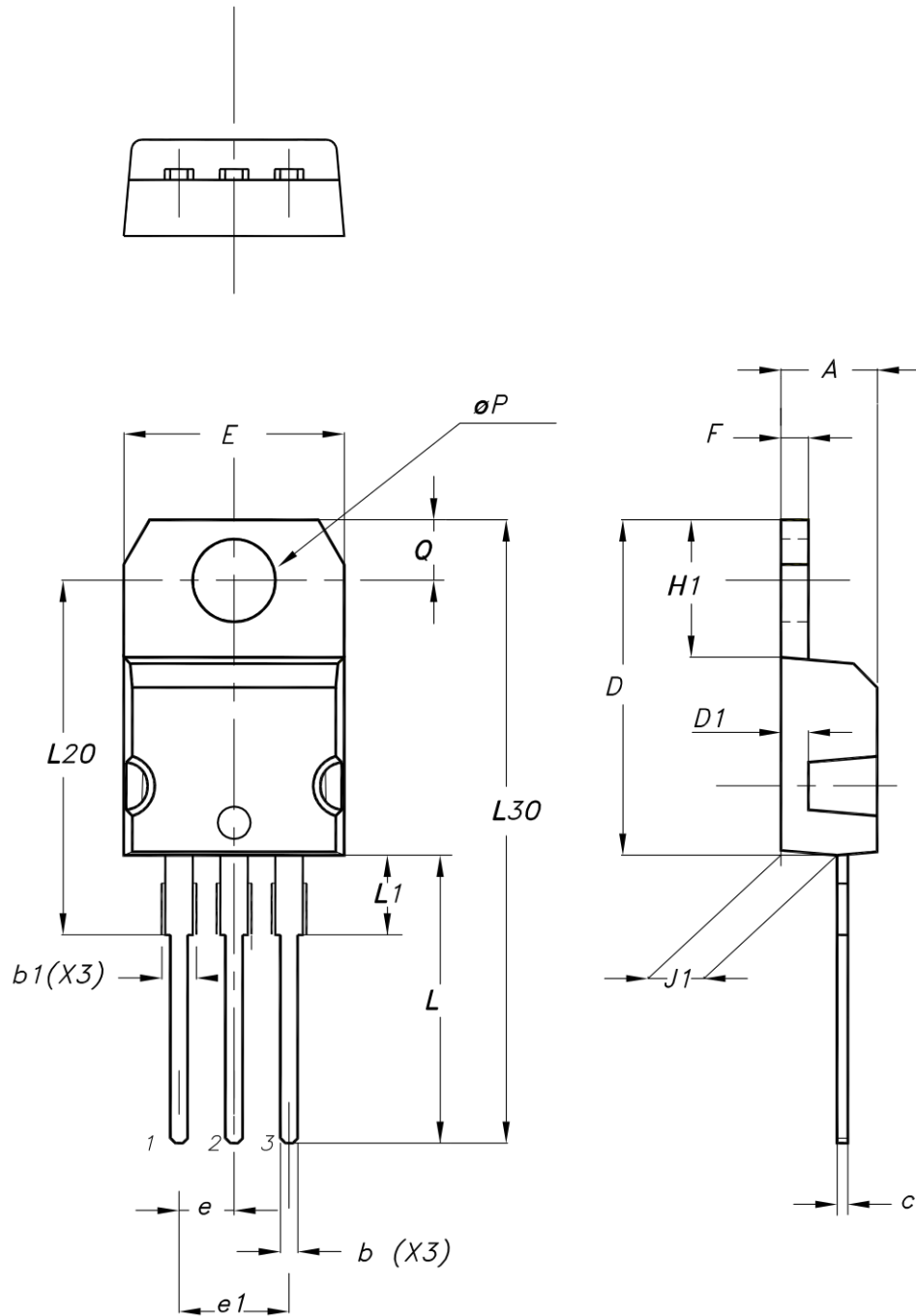


footprint_Rev_8

Note: Dimensions are in mm.

4.3 TO-220 type A package information

Figure 27. TO-220 type A package outline



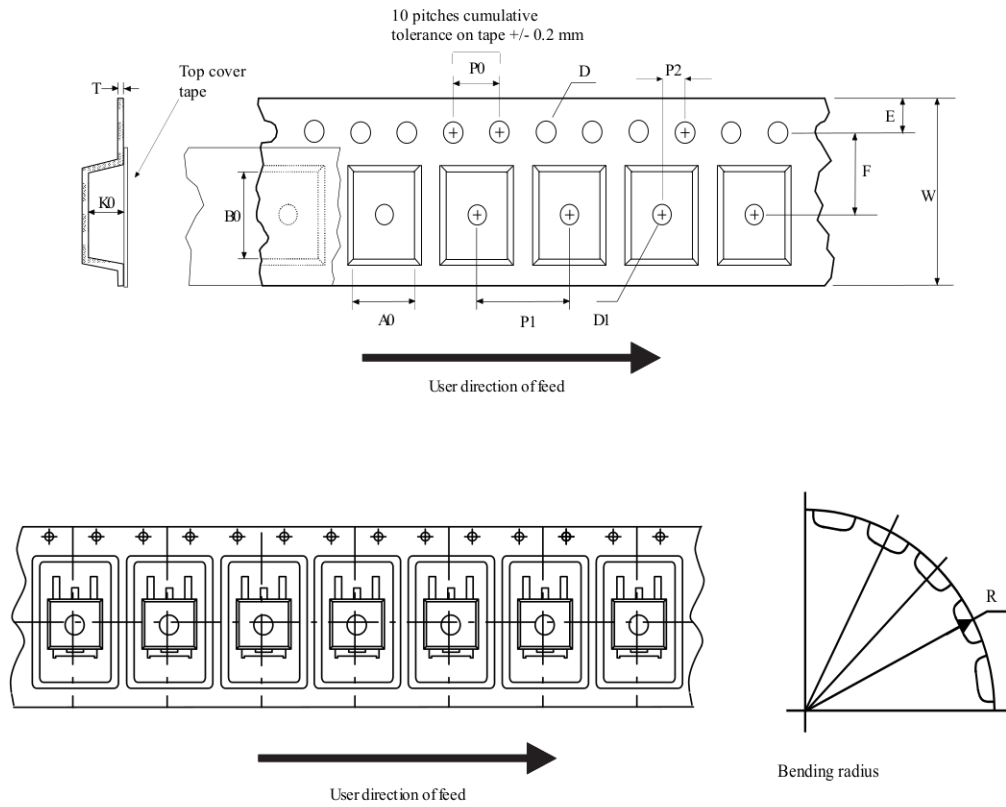
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Table 9. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

4.4 Packing information

Figure 28. Tape outline



AM08852v2

Figure 29. Reel outline

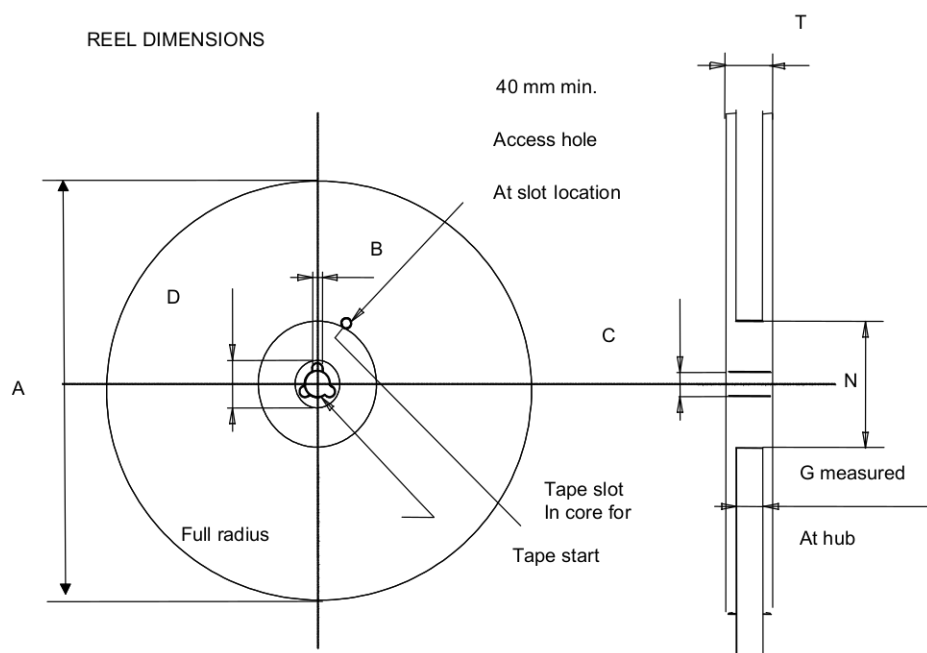


Table 10. Tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

5 Ordering information

Table 11. Order codes

Order codes	Marking	Package	Packing
STH270N8F7-2	270N8F7	H ² PAK-2	Tape and reel
STH270N8F7-6		H ² PAK-6	
STP270N8F7		TO-220	Tube

Revision history

Table 12. Document revision history

Date	Version	Changes
03-Dec-2012	1	First release.
09-Apr-2013	2	<ul style="list-style-type: none"> – Modified: $R_{DS(on)}$ max values on <i>Features</i> table, I_{DSS}, I_{GSS} values on <i>Table 4</i>, $R_{DS(on)}$ value for H²PAK-2, the entire typical values on <i>Table 5</i> and <i>6</i>, V_{SD} test conditions and max values, T_{RR}, Q_{RR}, I_{RRM} typical values on <i>Table 7</i> – Inserted: <i>Section 3: Electrical characteristics (curves)</i> – Document status promoted to preliminary data to production data – Added: H²PAK-6 package – Minor text changes
11-Oct-2013	3	<ul style="list-style-type: none"> – Modified: C_{rSS} typical value in <i>Table 5</i> – Updated: <i>Section 5: Package information</i> – Updated: <i>Figure 18, 19, 20</i> and <i>21</i> – Minor text changes
14-May-2015	4	<ul style="list-style-type: none"> – Updated title, features and description in cover page. – Minor text changes
12-Mar-2021	5	<ul style="list-style-type: none"> Modified Table 3. On/off states. Minor text changes.

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